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## **Contents**

Self-Reference Sensing for Improving Reliability and Bandwidth with 2T2MTJ STT	
MRAM Cell	1
Jang-Woo Ryu, Kee-Won Kwon	
A 100-MHz 256b-I/O 1-Mb Planar Nonvolatile STT-MRAM with Novel Memory	
Cells	5
Rui Wang, Hanan Dery, Michael Huang, Hui Wu	
An Energy-Efficient Hybrid (CMOS-MTJ) TCAM Using Stochastic Writes for Approxim	ıate
Computing	9
A. Kumar, M. Suri, V. Parmar, N. Locatelli, D. Querlioz	
Hybrid CMOS-OxRAM Based 4T-2R NVSRAM with Efficient Programming	
Scheme	. 14
Swatilekha Majumdar, Sandeep Kaur Kingra, Manan Suri and Manish Tikyani	
RAM and TCAM Designs by Using STT-MRAM	18
Bonan Yan, Zheng Li, Yiran Chen, Hai (Helen) Li	
Analysis of V <sub>th</sub> variability in NbO <sub>x</sub> -based threshold switches	23
S. Slesazeck, M. Herzig, T. Mikolajick, A. Ascoli, M. Weiher, R. Tetzlaff	
Localized Metal Doping Effect on Switching Behaviors of TaOx-based RRAM	
Device	28
Zongwei Wang, Jian Kang, Yichen Fang, Zhizhen Yu, Xue Yang, Yimao Cai,	
Yangyuan Wang, Ru Huang	
High Endurance Strategies for Hafnium Oxide Based Ferroelectric Field Effect	
Transistor	31
J. Müller, P. Polakowski, S. Müller, H. Mulaosmanovic,	
J. Ocker, T. Mikolajick, S. Slesazeck, S. Flachowsky, M. Trentzsch	